Semiconductor Manufacturing Technology

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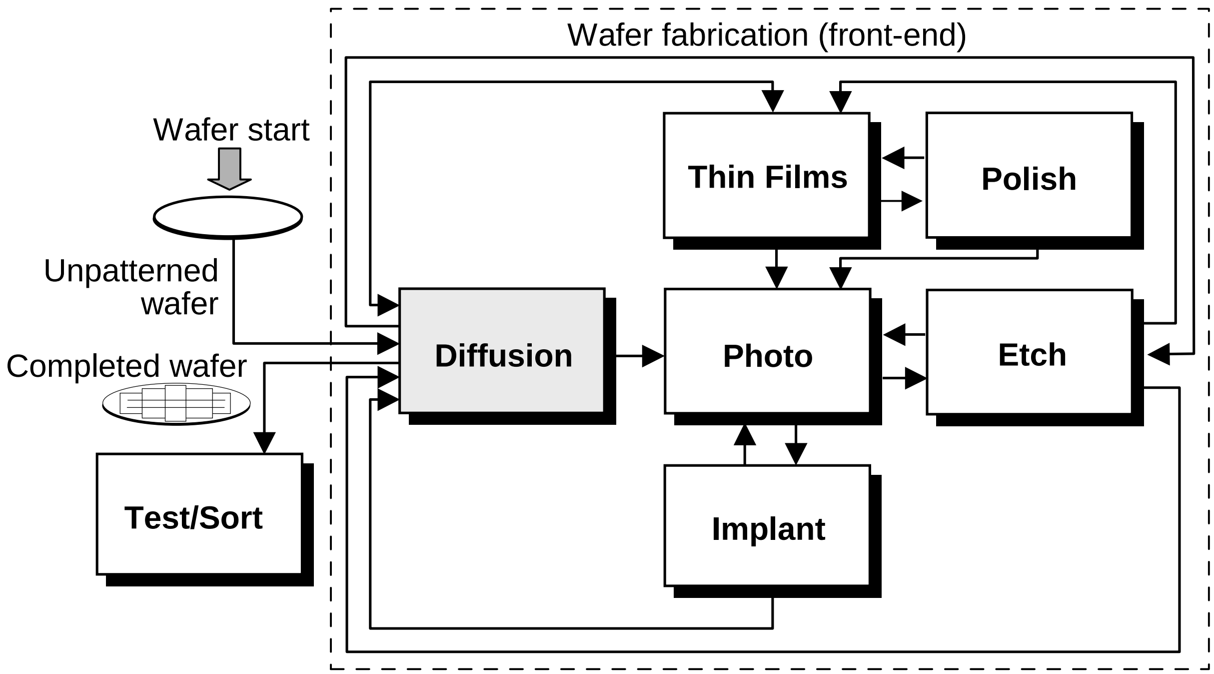
Chapter 10

Oxidation

Diffusion Area of Wafer Fabrication



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Oxide Film

- Nature of Oxide Film
- Uses of Oxide Film
  - Device Protection and Isolation
  - Surface Passivation
  - Gate Oxide Dielectric
  - Dopant Barrier
  - Dielectric Between Metal Layers

Atomic Structure of Silicon Dioxide

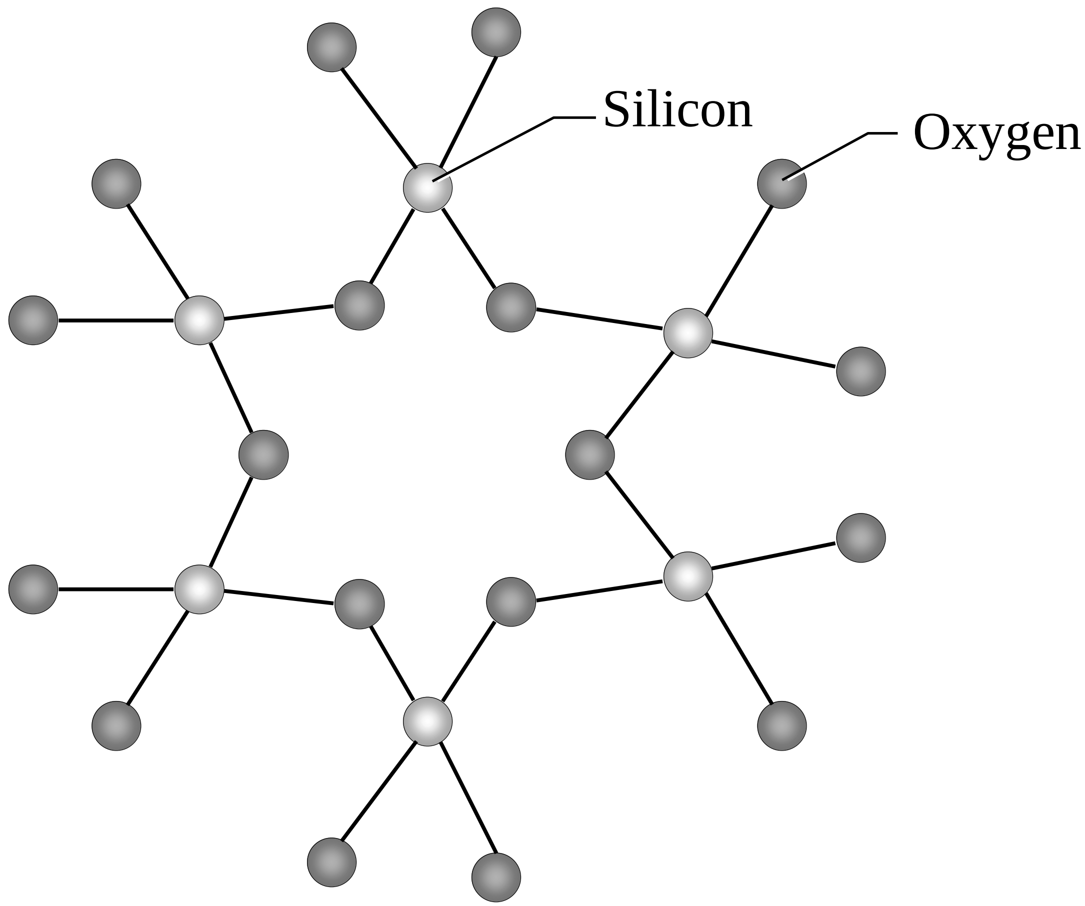

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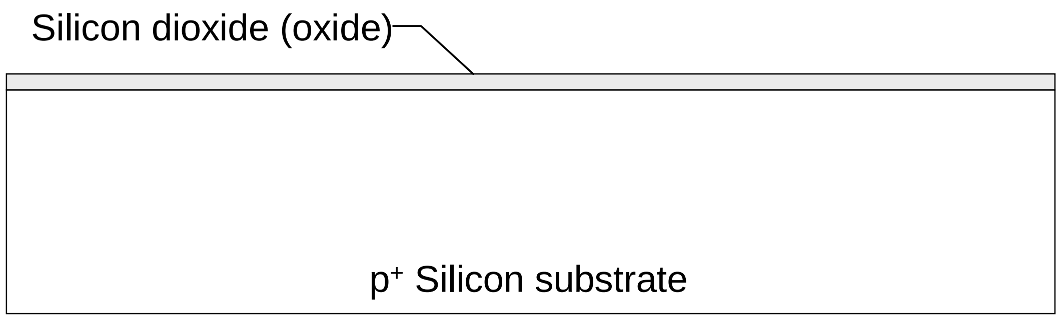
Table 10.1
Oxide Applications: Native Oxide

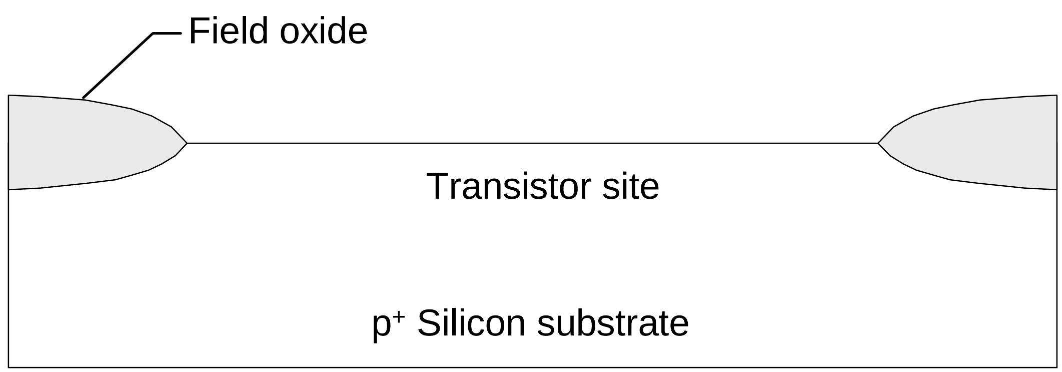
Purpose: This oxide is a contaminant and generally undesirable. Sometimes used in memory storage or film passivation.



Comments: Growth rate at room temperature is 15 per hour up to about 40 Å.

Table 10.1
Oxide Applications: Field Oxide

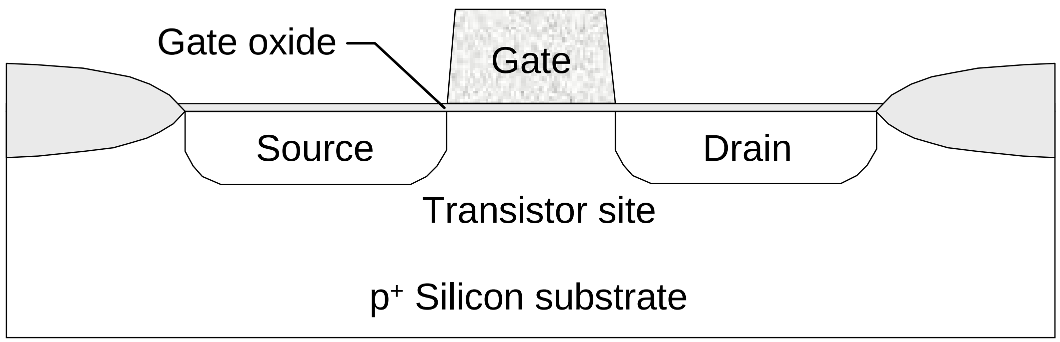
Purpose:	Serves as an isolation barrier between individual transistors to isolate them from each other.



Comments:	Common field oxide thickness range from 2,500 Å to 15,000 Å. Wet oxidation is the preferred method.

Table 10.1
Oxide Applications: <u>Gate Oxide</u>

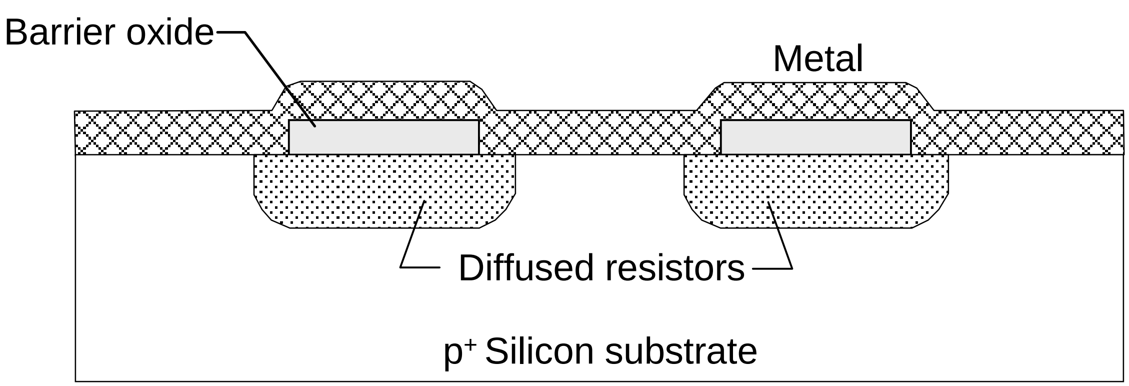
Purpose:	Serves as a dielectric between the gate and source-drain parts of MOS transistor.



Comments:	Growth rate at room temperature is 15 Å per hour up to about 40 Å. Common gate oxide film thickness range from about 30 Å to 500 Å. Dry oxidation is the preferred method.

Table 10.1
Oxide Applications: Barrier Oxide

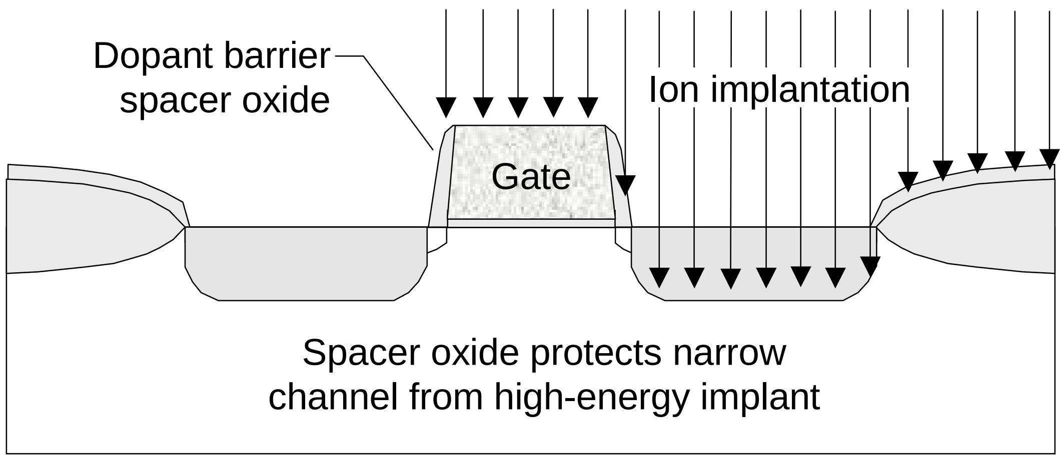
Purpose:	Protect active devices and silicon from follow-on processing.



Comments:	Thermally grown to several hundred Angstroms thickness.

Table 10.1
Oxide Applications: Dopant Barrier

Purpose:	Masking material when implanting dopant into wafer. Example: Spacer oxide used during the implant of dopant into the source and drain regions.



Comments:	Dopants diffuse into unmasked areas of silicon by selective diffusion.

Table 10.1
Oxide Applications: Pad Oxide

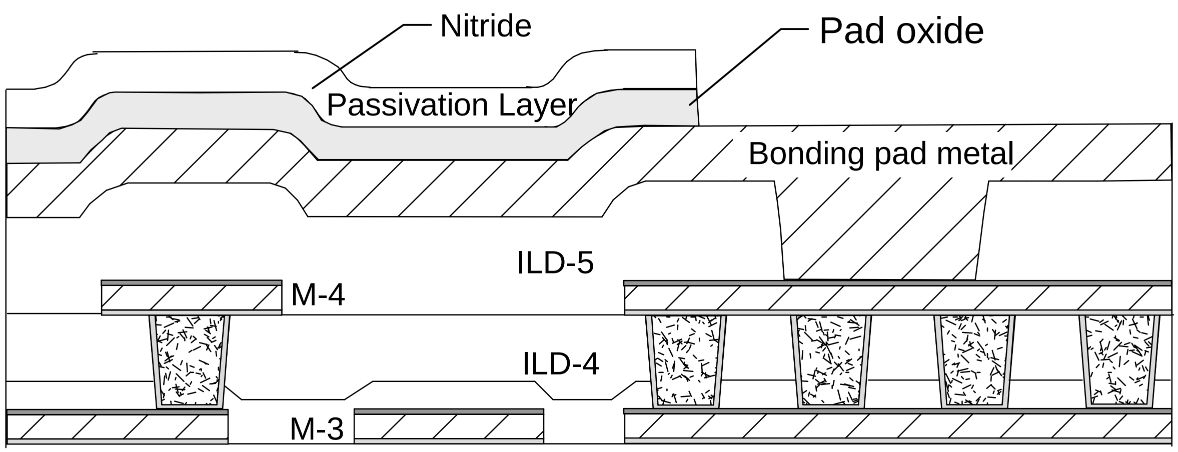
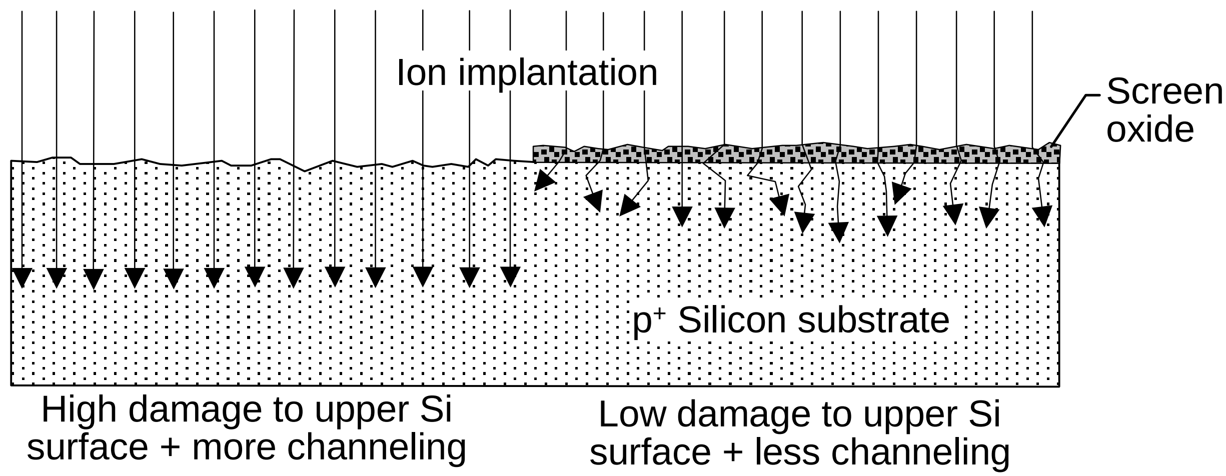
Purpose: Provides stress reduction for Si_3N_4

Comments: Thermally grown and very thin.

Table 10.1
Oxide Applications: Implant Screen Oxide

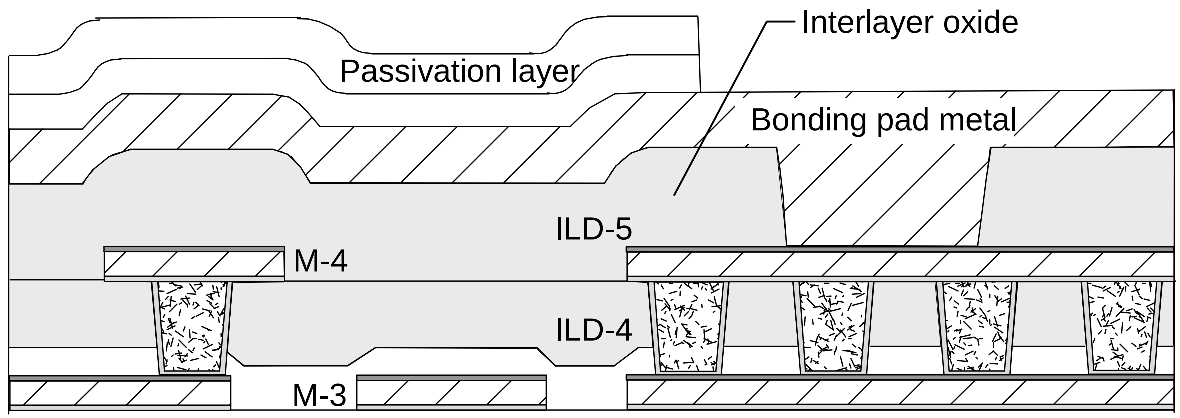
Purpose:	Sometimes referred to as "sacrificial oxide", screen oxide, is used to reduce implant channeling and damage. Assists creation of shallow junctions.



Comments: Thermally grown

Table 10.1
Oxide Applications: Insulating Barrier between Metal Layers

Purpose: Serves as protective layer between metal lines.



Comments: This oxide is not thermally grown, but is deposited.

Thermal Oxidation Growth

- Chemical Reaction for Oxidation
  - Dry oxidation
  - Wet oxidation
- Oxidation Growth Model
  - Oxide silicon interface
    - Use of chlorinated agents in oxidation
  - Rate of oxide growth
  - Factors affecting oxide growth
  - Initial growth phase
  - Selective oxidation
    - LOCOS
    - STI

Oxide Thickness Ranges for Various Requirements

Semiconductor Application	**Typical Oxide Thickness, Å**
Gate oxide (0.18 μm generation)	20 – 60
Capacitor dielectrics	5 – 100
Dopant masking oxide	400 – 1,200 (Varies depending on dopant, implant energy, time & temperature)
STI Barrier Oxide	150
LOCOS Pad Oxide	200 – 500
Field oxide	2,500 – 15,000

Dry Oxidation Time (Minutes)

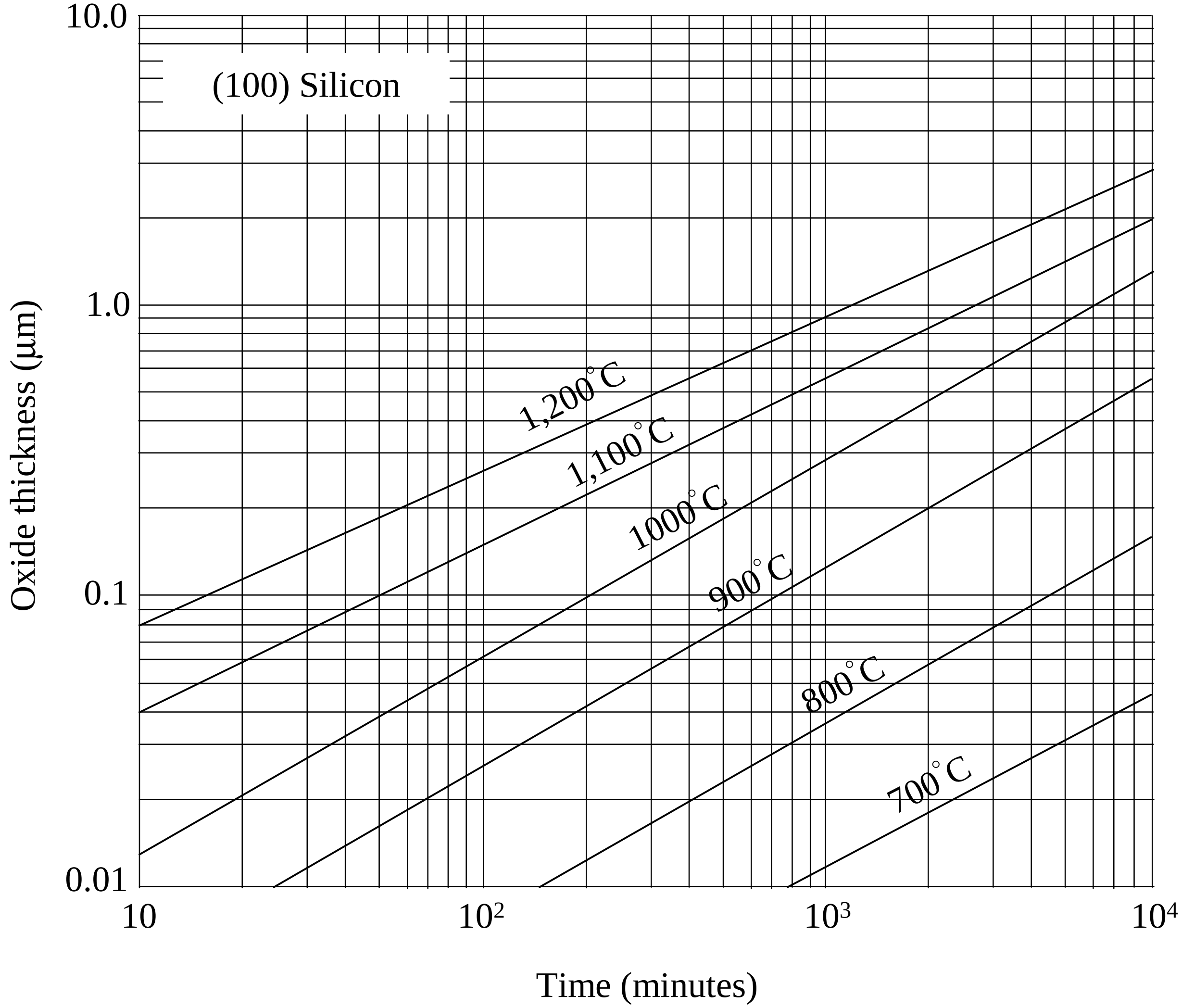


Figure 10.6

Wet Oxygen Oxidation

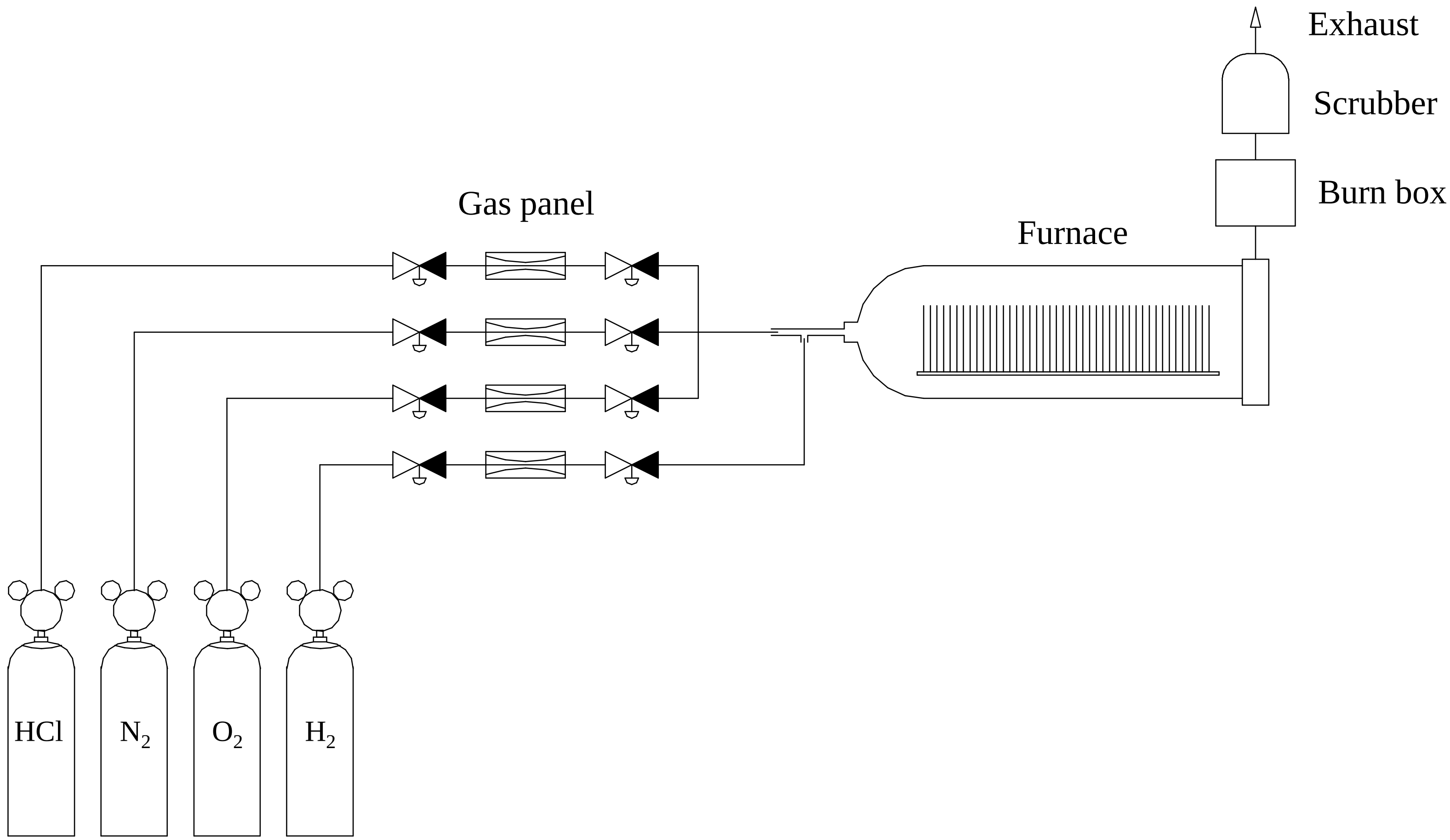
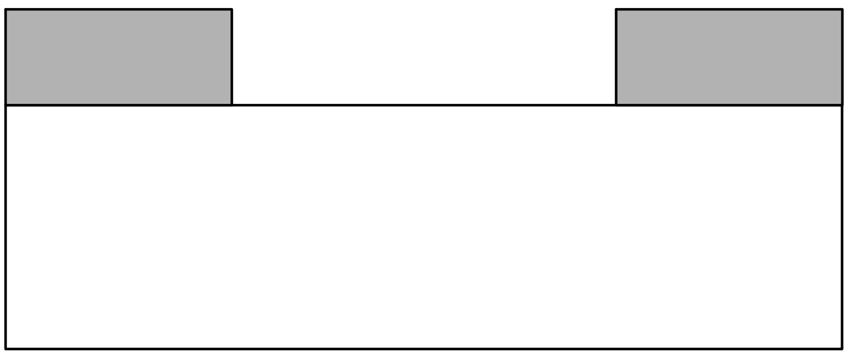


Figure 10.7

Consumption of Silicon during Oxidation



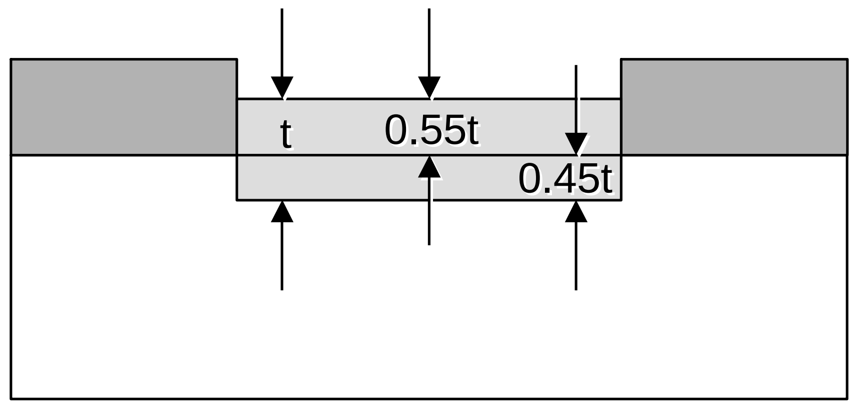
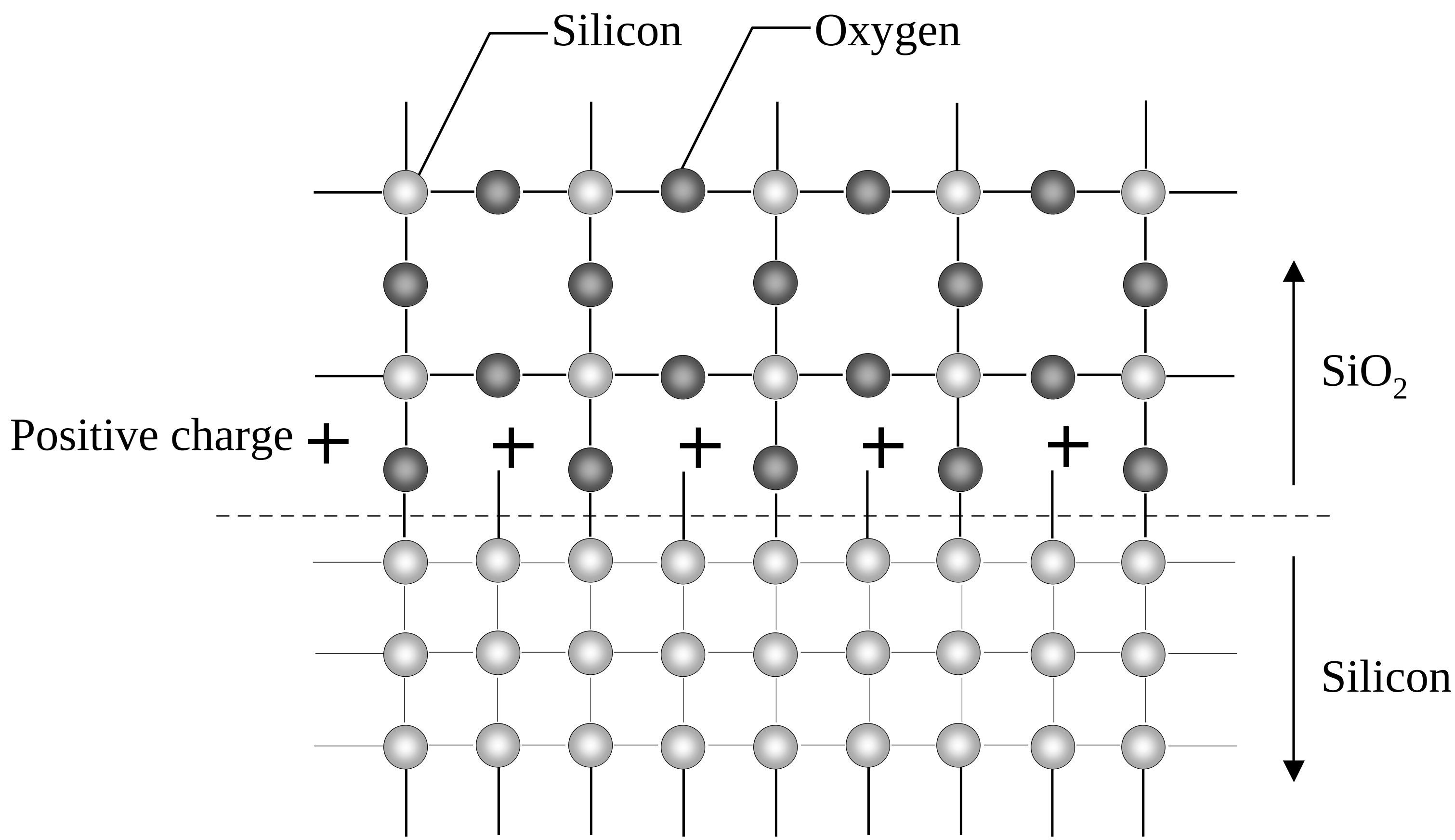


Figure 10.8

Charge Buildup at Si/SiO2 Interface



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Diffusion of Oxygen Through Oxide Layer

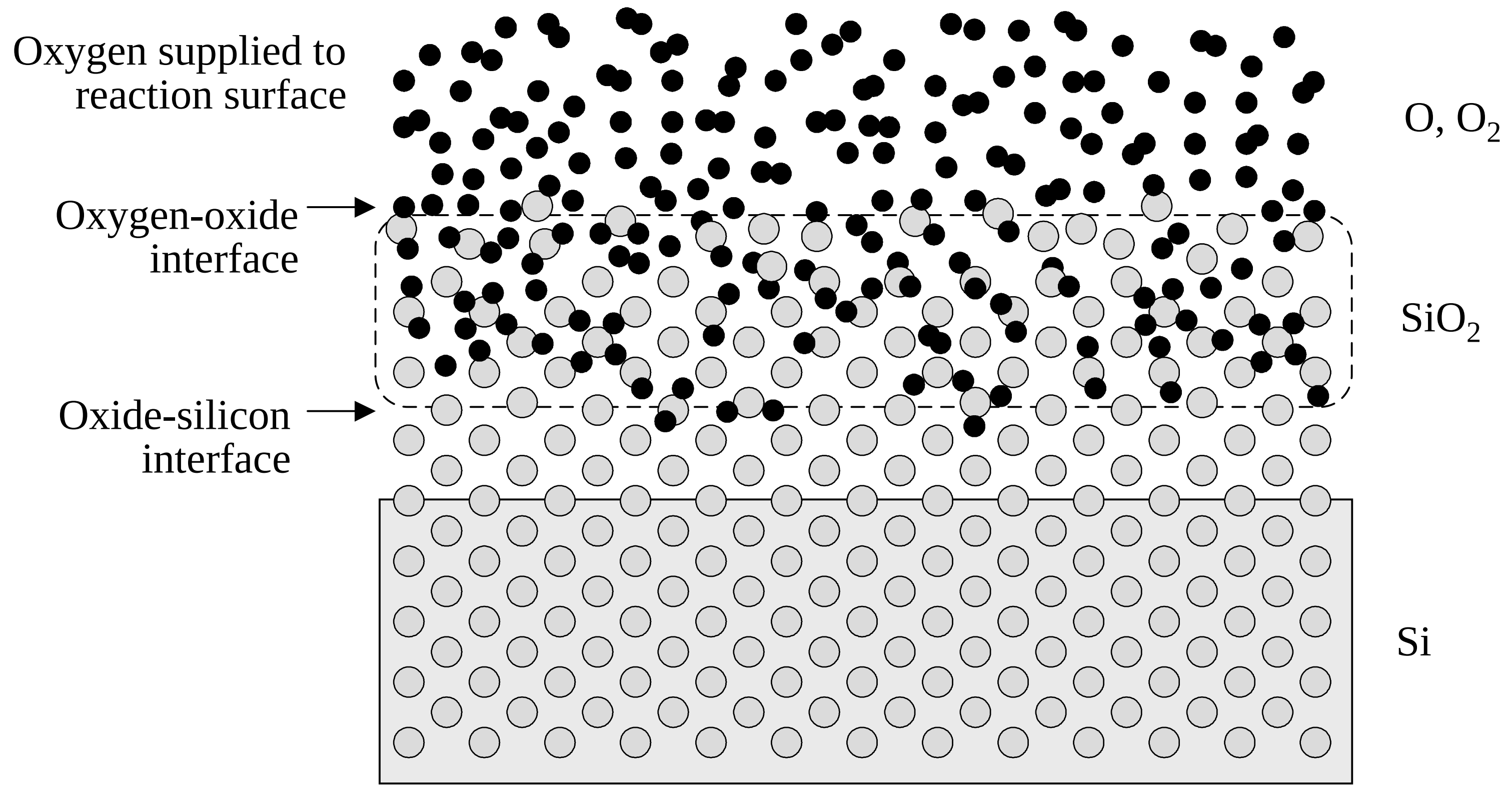

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Figure 10.11

Linear & Parabolic Stages for Dry Oxidation Growth at 1100ºC

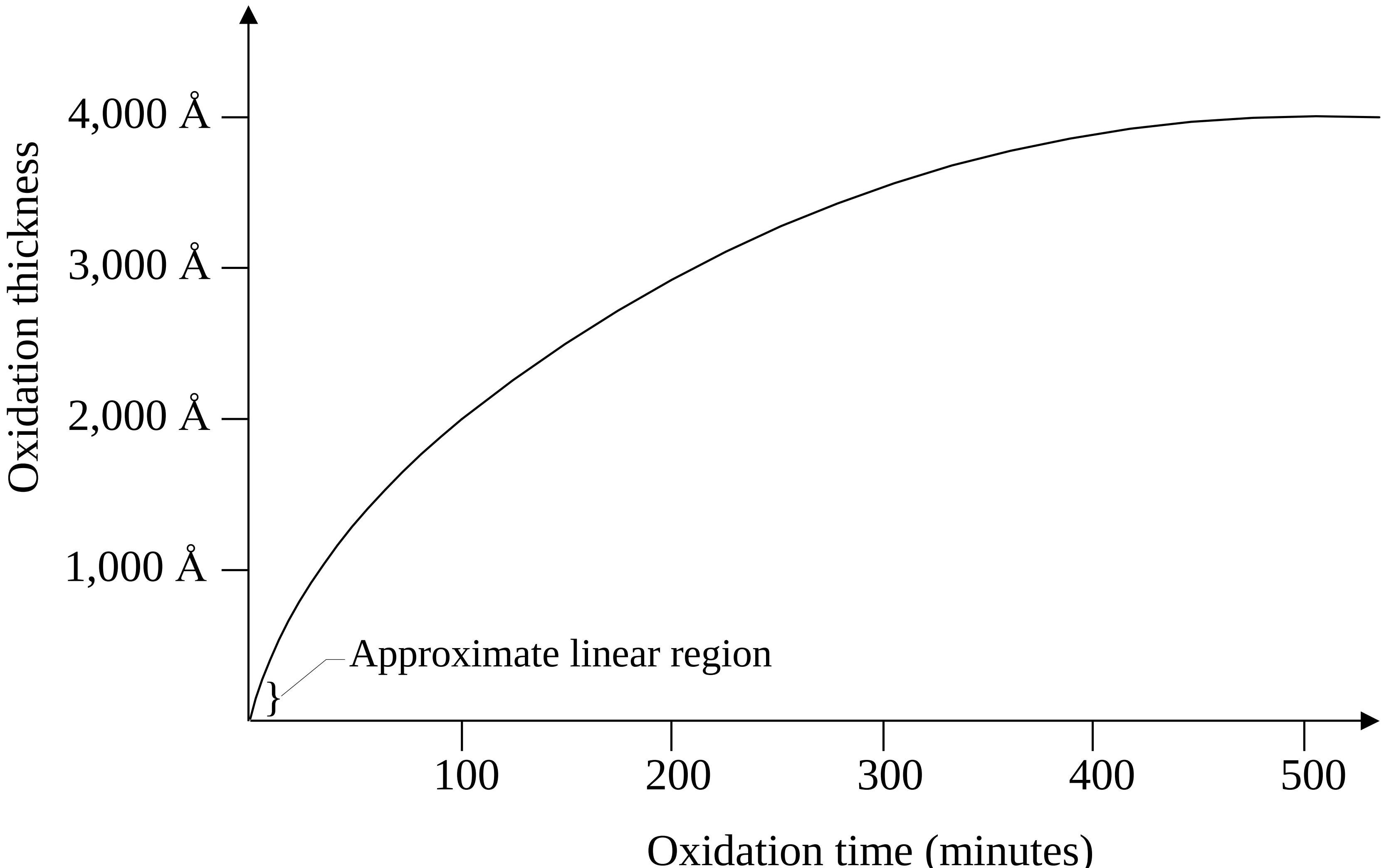

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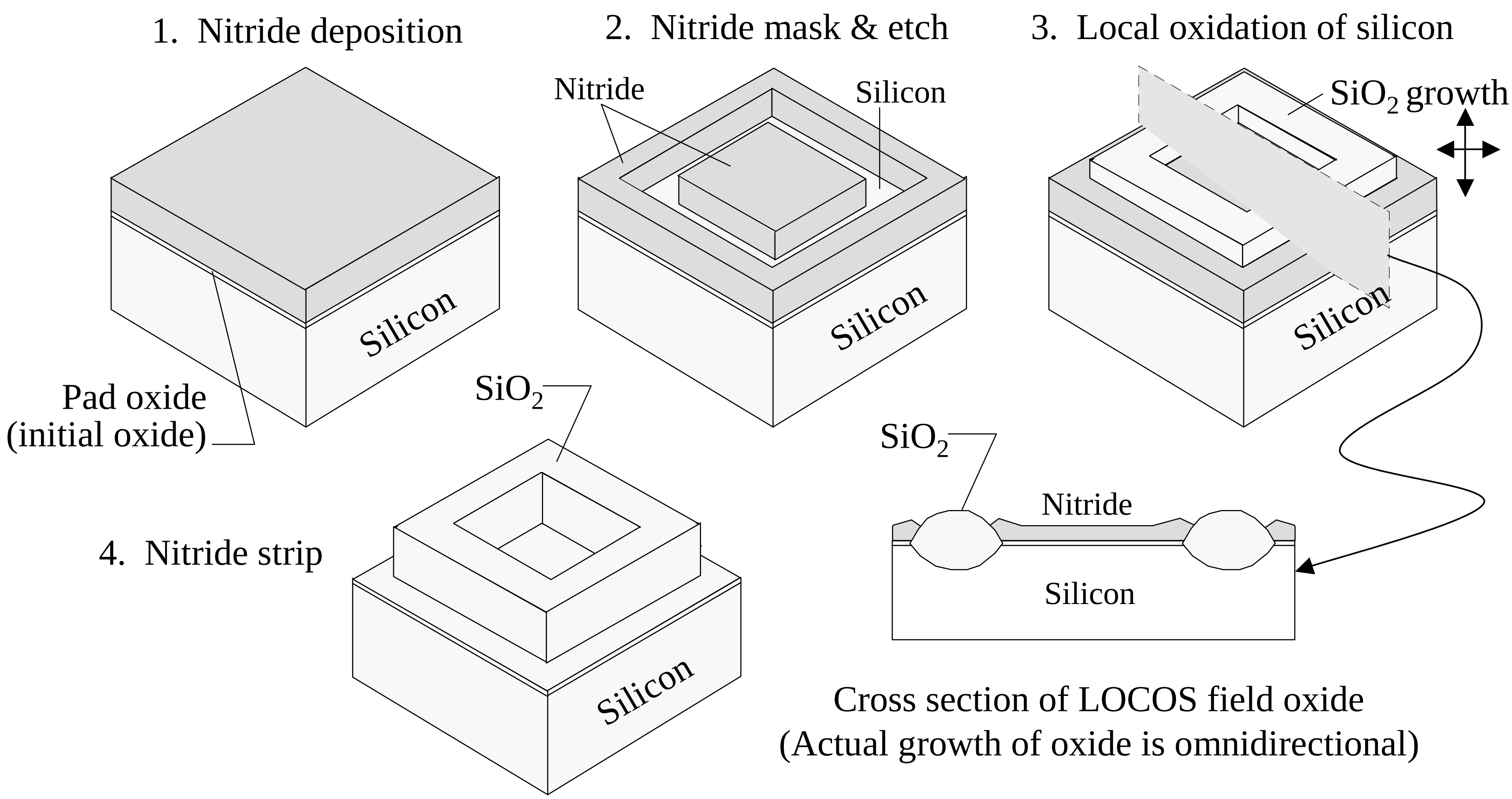
Figure 10.12

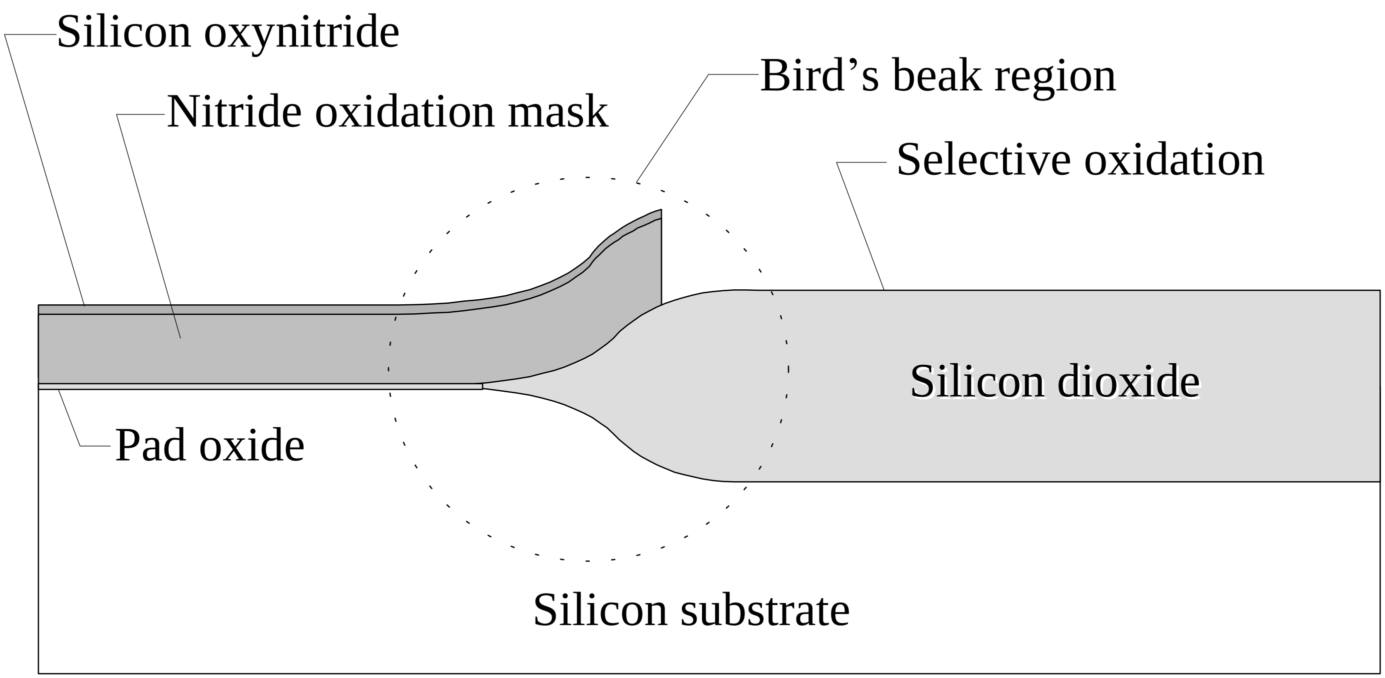
LOCOS Process



Cross section of LOCOS field oxide
(Actual growth of oxide is omnidirectional)

Figure 10.13

Selective Oxidation and Bird's Beak Effect



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STI Oxide Liner

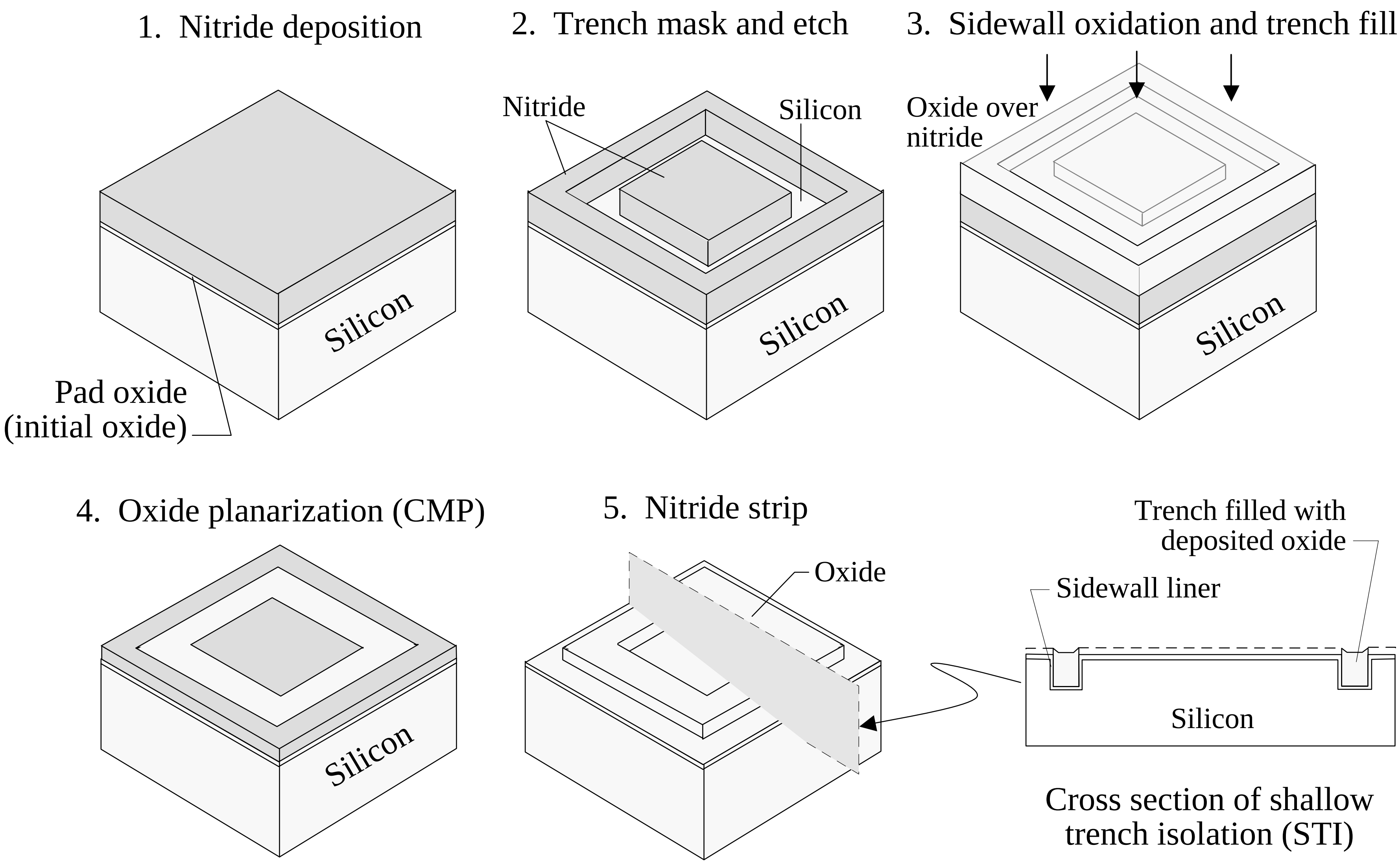

Figure 10.15

Furnace Equipment

- Horizontal Furnace
- Vertical Furnace
- Rapid Thermal Processor (RTP)

Horizontal and Vertical Furnaces

Performance Factor	Performance Objective	Horizontal Furnace	Vertical Furnace
Typical wafer loading size	Small, for process flexibility	200 wafers/batch	100 wafers/batch
Clean room footprint	Small, to use less space	Larger, but has 4 process tubes	Smaller (single process tube)
Parallel processing	Ideal for process flexibility	Not capable	Capable of loading/unloading wafers during process, which increases throughput
Gas flow dynamics (GFD)	Optimize for uniformity	Worse due to paddle and boat hardware. Bouyancy and gravity effects cause non-uniform radial gas distribution.	Superior GFD and symmetric/uniform gas distribution
Boat rotation for improved film uniformity	Ideal condition	Impossible to design	Easy to include
Temperature gradient across wafer	Ideally small	Large, due to radiant shadow of paddle	Small
Particle control during loading/unloading	Minimum particles	Relatively poor	Improved particle control from top-down loading scheme
Quartz change	Easily done in short time	More involved and slow	Easier and quicker, leading to reduced downtime
Wafer loading technique	Ideally automated	Difficult to automate in a successful fashion	Easily automated with robotics
Pre-and post-process control of furnace ambient	Control is desirable	Relatively difficult to control	Excellent control, with options of either vacuum or neutral ambient

Table 10.3

Horizontal Diffusion Furnace

Photograph courtesy of International SEMATECH

Vertical Diffusion Furnace

Photograph courtesy of International SEMATECH

Block Diagram of Vertical Furnace System

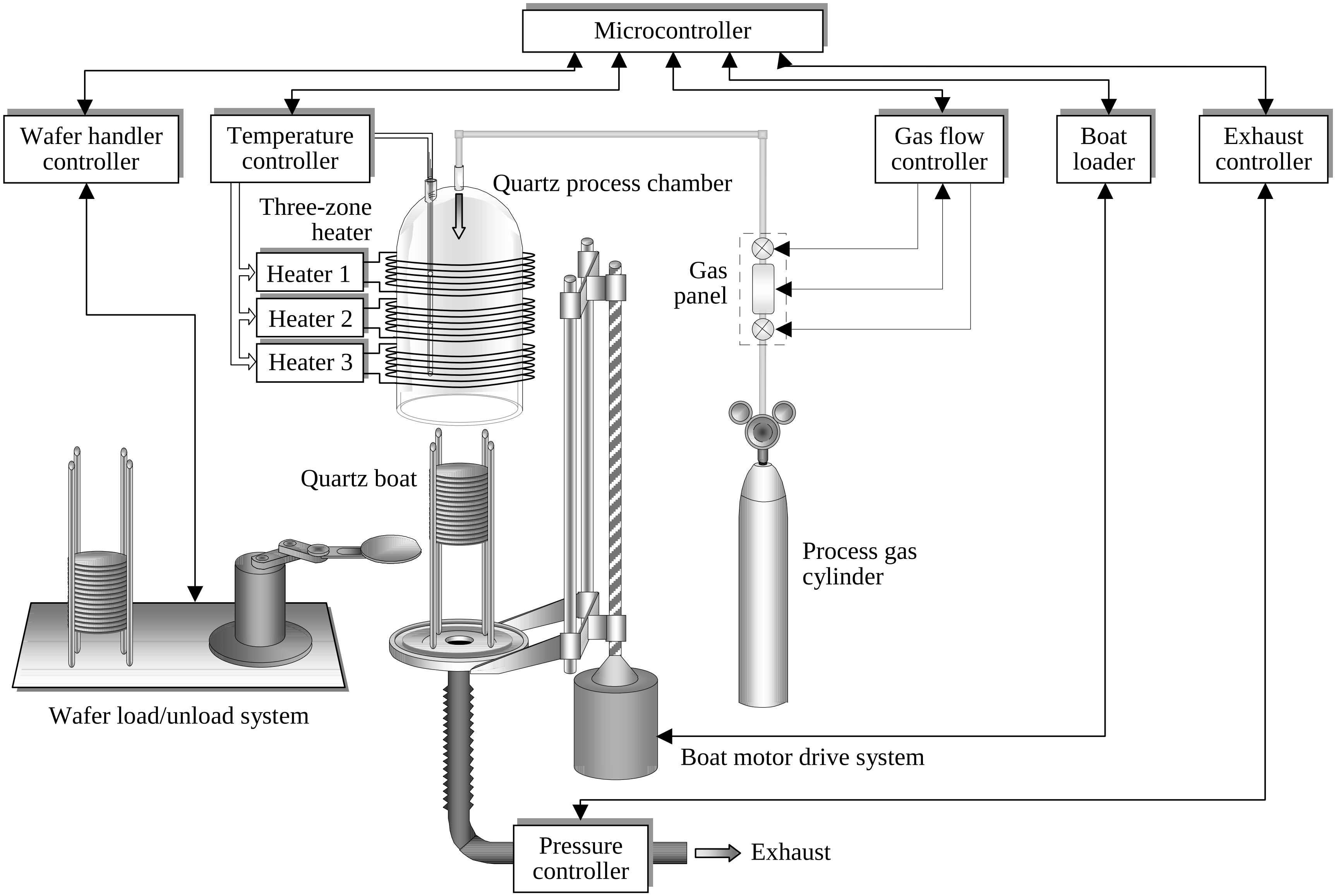

Figure 10.16

Common Gases used in Furnace Processes

Gases	Classifications	Examples
Bulk	Inert gas	Argon (Ar), Nitrogen (N_2)
	Reducing gas	Hydrogen (H_2)
	Oxidizing gas	Oxygen (O_2)
Specialty	Silicon-precursor gas	Silane (SiH_4), dichlorosilane (DCS) or (H_2SiCl_2)
	Dopant gas	Arsine (AsH_3), phosphine (PH_3) Diborane (B_2H_6)
	Reactant gas	Ammonia (NH_3), hydrogen chloride (HCl)
	Atmospheric/purge gas	Nitrogen (N_2), helium (He)
	Other specialty gases	Tungsten hexafluoride (WF_6)

Table 10.4

Burn Box to Combust Exhaust

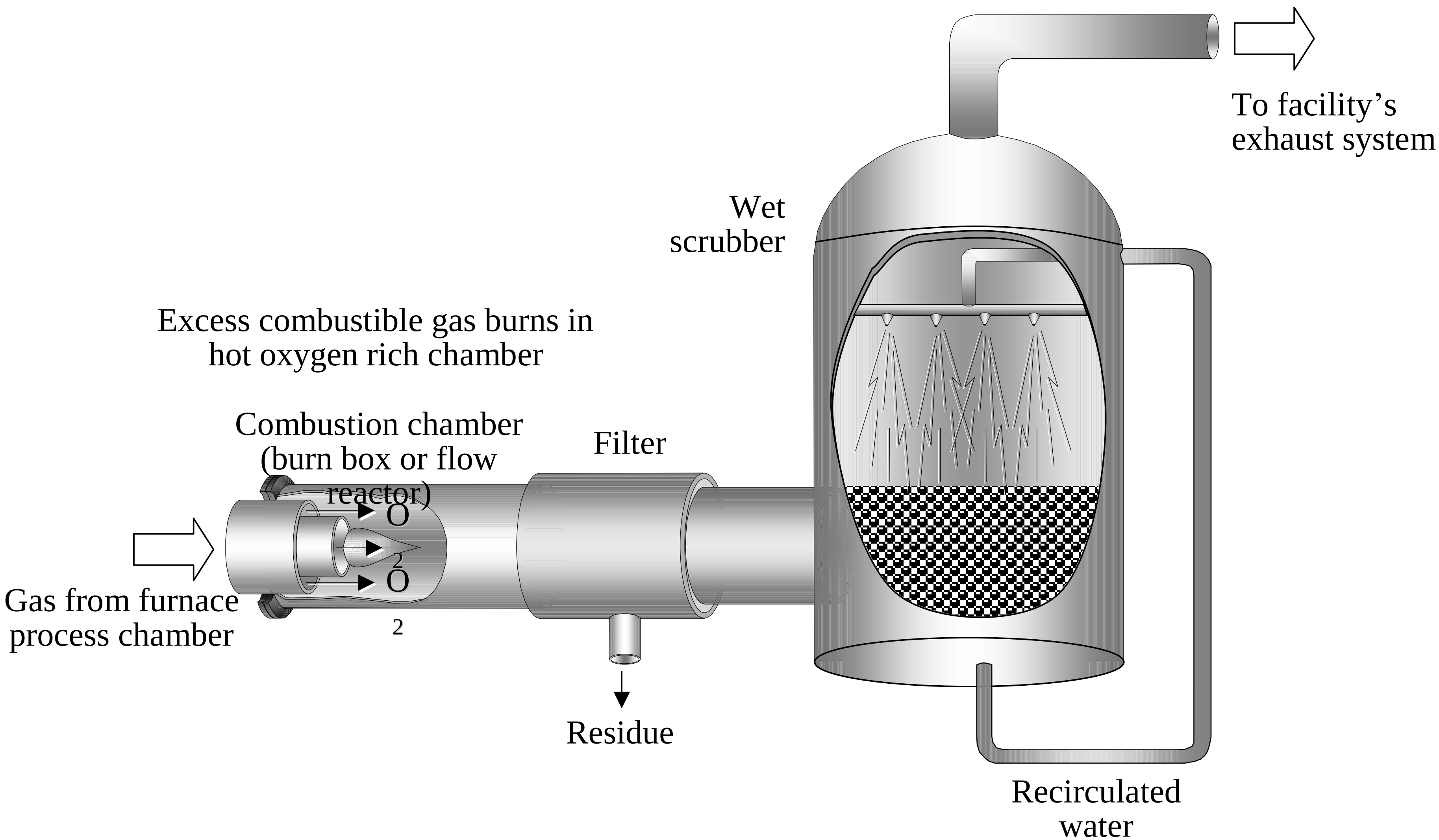

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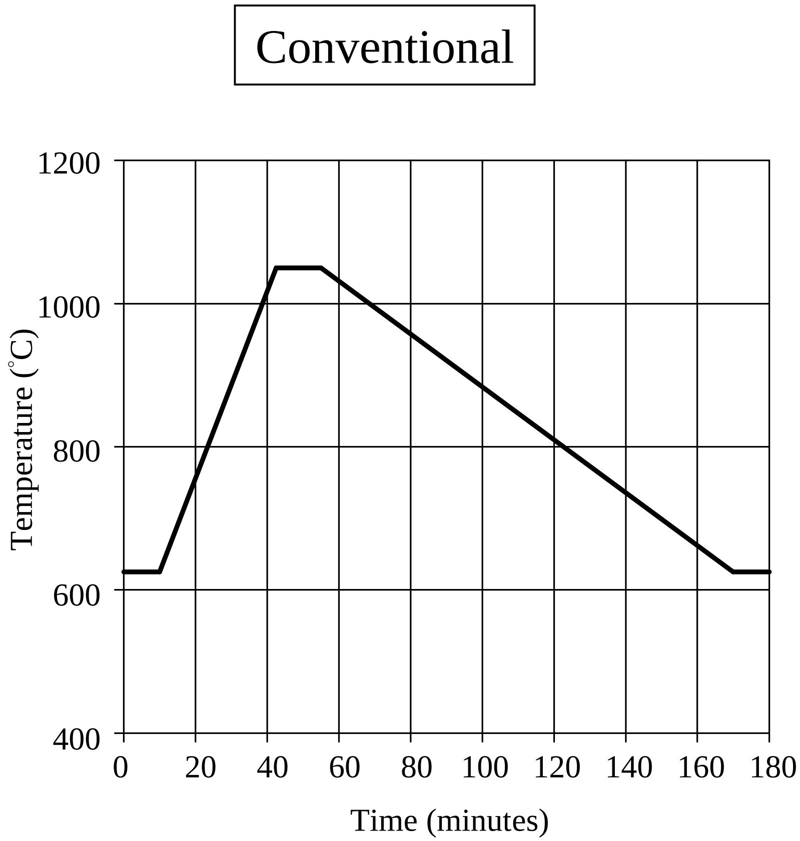
Figure 10.20

Thermal Profile of Conventional Versus Fast Ramp Vertical Furnace



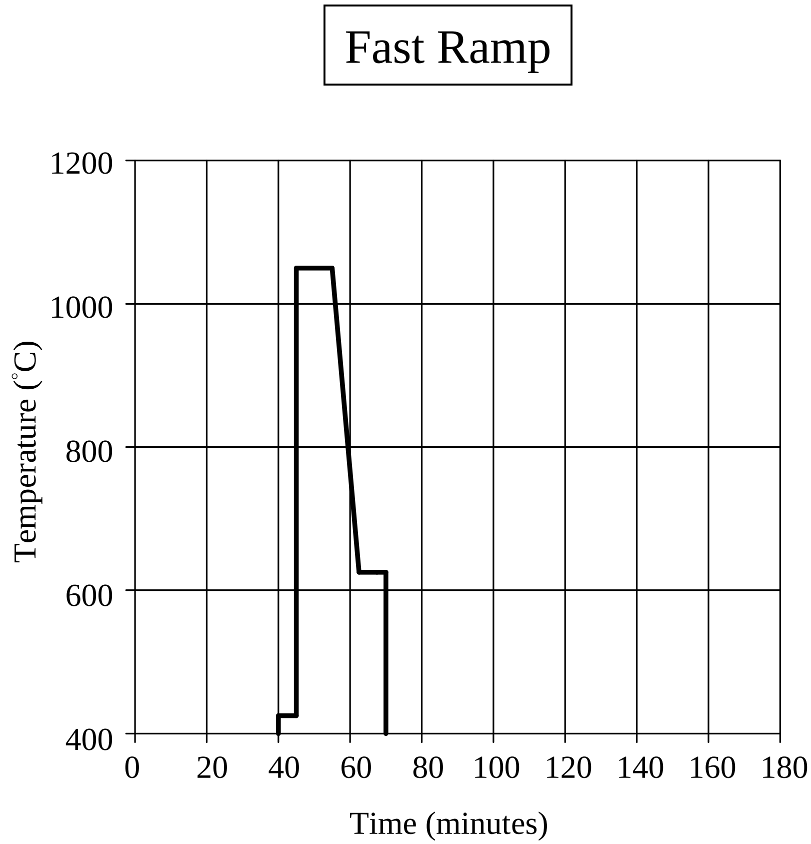


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Figure 10.21

The Main Advantages of a Rapid Thermal Processor

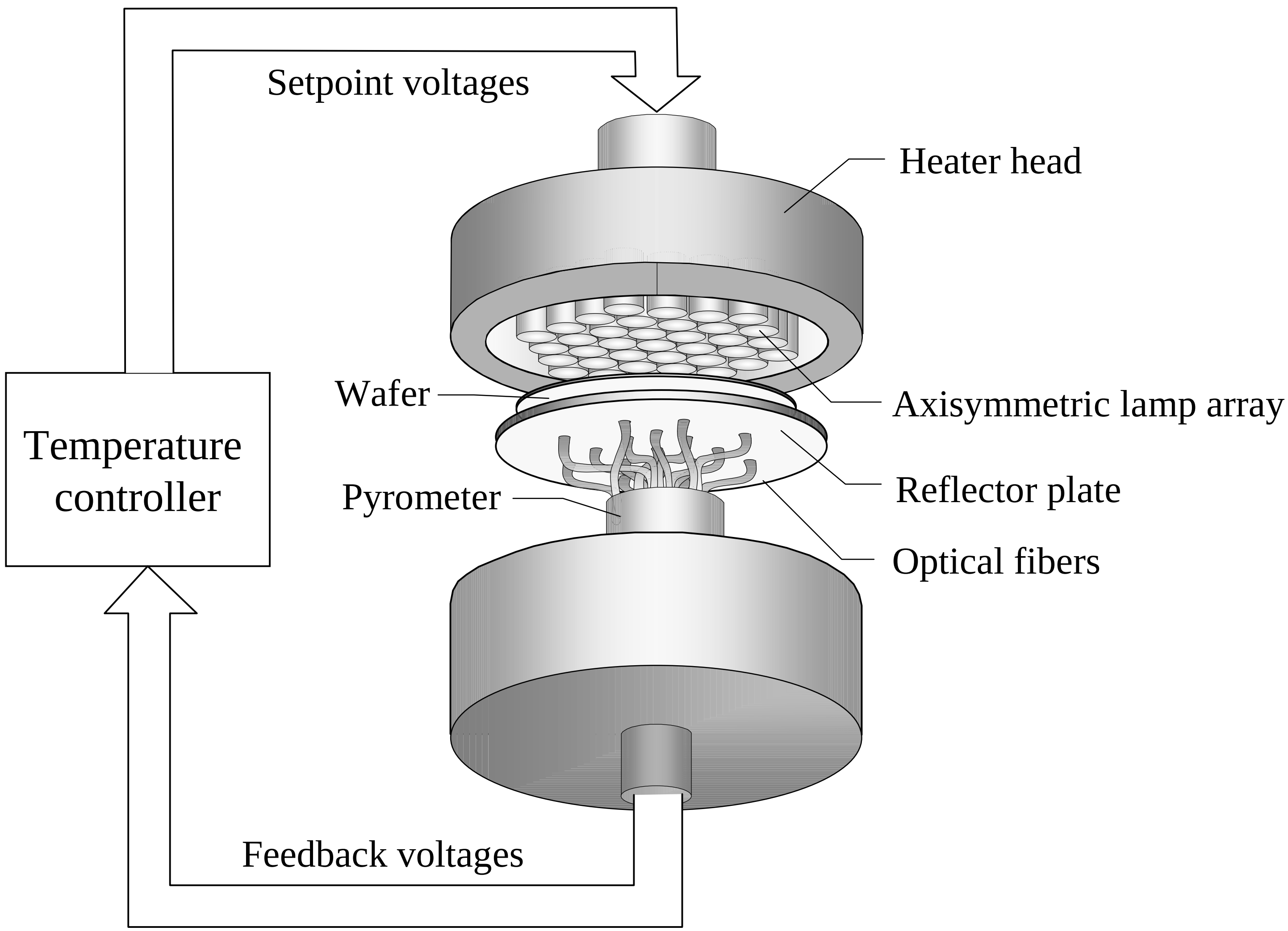
- Reduced thermal budget
- Minimized dopant movement in the silicon
- Ease of clustering multiple tools
- Reduced contamination due to cold wall heating
- Cleaner ambient because of the smaller chamber volume
- Shorter time to process a wafer (referred to as cycle time)

Comparison of Conventional Vertical Furnace and RTP

Vertical Furnace	**RTP**
Batch	Single-wafer
Hot wall	Cold wall
Long time to heat and cool batch	Short time to heat and cool wafer
Small thermal gradient across wafer	Large thermal gradient across wafer
Long cycle time	Short cycle time
Ambient temperature measurement	Wafer temperature measurement
Issues:	Issues:
Large thermal budget	Temperature uniformity
Particles	Minimize dopant movement
Ambient control	Repeatability from wafer to wafer
	Throughput
	Wafer stress due to rapid heating
	Absolute temperature measurement

Table 10.5

Rapid Thermal Processor



RTP Applications

- Anneal of implants to remove defects and activate and diffuse dopants
- Densification of deposited films, such as deposited oxide layers
- Borophosphosilicate glass (BPSG) reflow
- Anneal of barrier layers, such as titanium nitride (TiN)
- Silicide formation, such as titanium silicide ($TiSi_2$)
- Contact alloying

Oxidation Process

- Pre Oxidation Cleaning
  - Oxidation process recipe
- Quality Measurements
- Oxidation Troubleshooting

Critical Issues for Minimizing Contamination

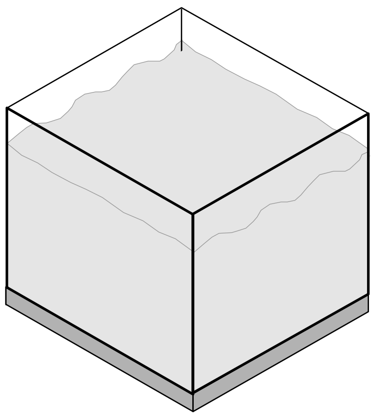
- Maintenance of the furnace and associated equipment (especially quartz components) for cleanliness
- Purity of processing chemicals
- Purity of oxidizing ambient (the source of oxygen in the furnace)
- Wafer cleaning and handling practices

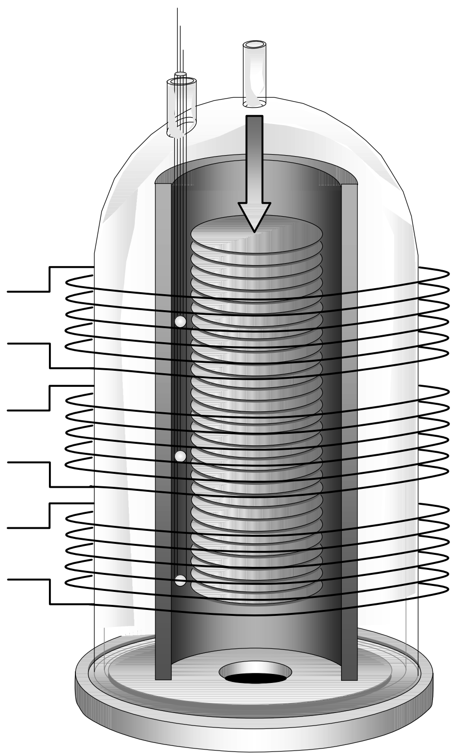
Thermal Oxidation Process Flow Chart

Wet Clean
- Chemicals
- % solution
- Temperature
- Time

Oxidation Furnace
- O_2, H_2 , N_2 , Cl
- Flow rate
- Exhaust
- Temperature
- Temperature profile
- Time

Inspection
- Film thickness
- Uniformity
- Particles
- Defects





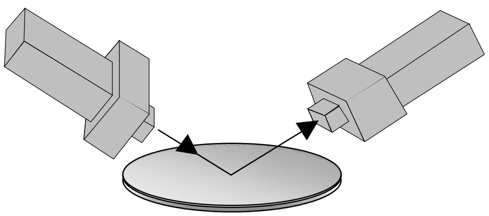


Figure 10.23

Process Recipe for Dry Oxidation Process

Step	Time (min)	Temp (ºC)	N_2 Purge Gas (slm)	Process Gas N_2 (slm)	Process Gas O_2 (slm)	Process Gas HCl (sccm)	Comments
0		850	8.0	0	0	0	Idle condition
1	5	850		8.0	0	0	Load furnace tube
2	7.5	Ramp 20ºC/min		8.0	0	0	Ramp temperature up
3	5	1000		8.0	0	0	Temperature stabilization
4	30	1000		0	2.5	67	Dry oxidation
5	30	1000		8.0	0	0	Anneal
6	30	Ramp -5ºC/min		8.0	0	0	Ramp temperature down
7	5	850		8.0	0	0	Unload furnace tube
8		850	8.0	0	0	0	Idle

Note: gas flow units are slm (standard liters per minute) and sccm (standard cubic centimeters per minute)

Table 10.6

Wafer Loading Pattern in Vertical Furnace

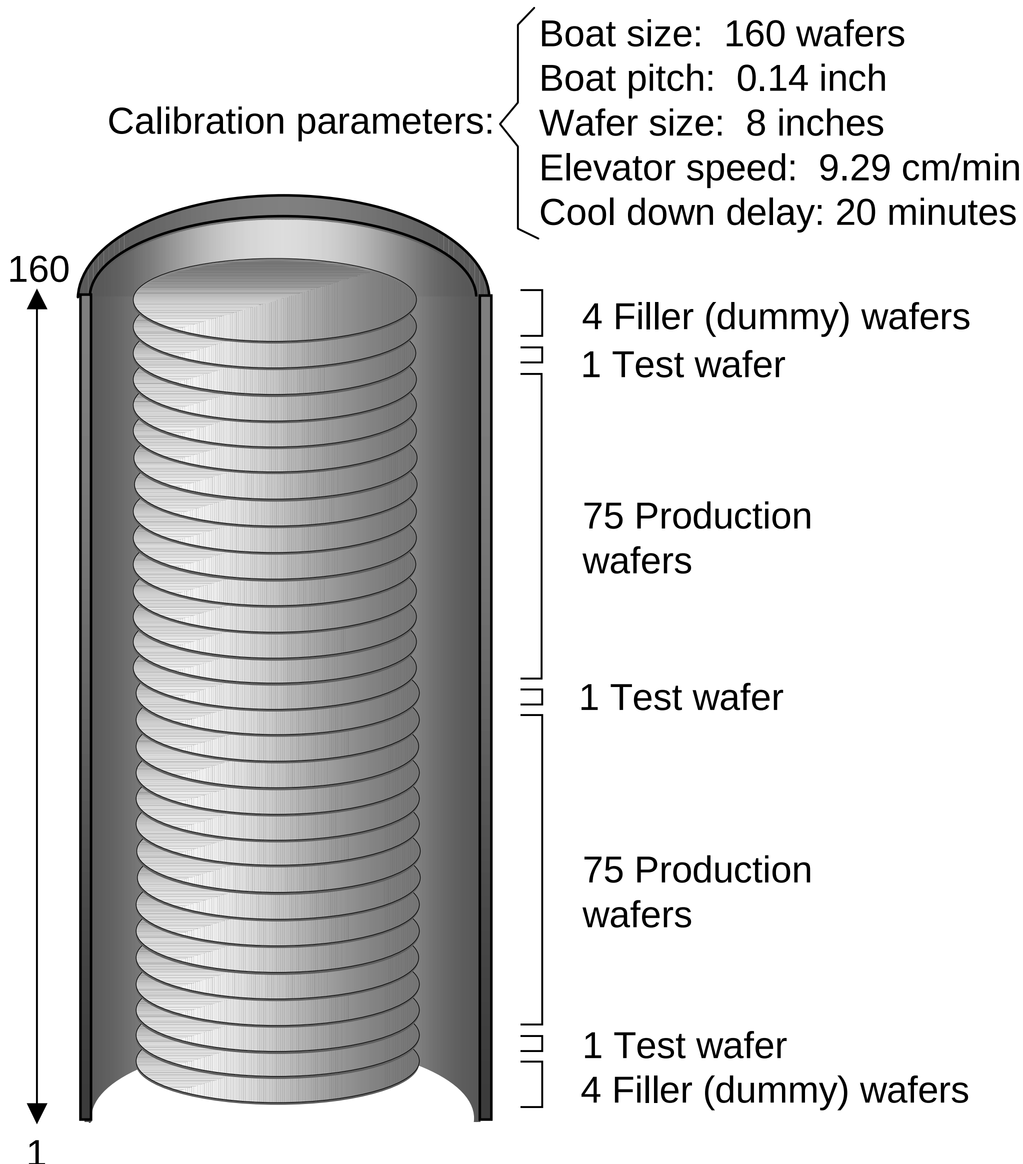


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Figure 10.24